

**AMENDMENTS TO THE CLAIMS:**

*Please amend the claims as follows:*

1-7. (Cancelled)

8. (New) A solid-state imaging apparatus comprising:

a substrate;

a first pixel formed on the substrate including a first photodiode, a first transfer transistor and a first floating diffusion;

a second pixel formed on the substrate adjacent to the first pixel including a second photodiode, a second transfer transistor and a second floating diffusion;

a reset transistor formed on the substrate; and

an amplifier transistor formed on the substrate,

wherein a gate electrode of the amplifier transistor is connected to the first floating diffusion and the second floating diffusion,

a source of the reset transistor is connected to the first floating diffusion and the source of the reset transistor is connected to the second floating diffusion, and

a distance and direction from the first photodiode to the first floating diffusion are substantially equal to a distance and direction from the second photodiode to the second floating diffusion.

9. (New) The solid-state imaging apparatus of claim 8, further comprising:

a power supply interconnect; and

an output interconnect,

wherein the power supply interconnect is connected to a drain of the reset transistor and a source of the amplifier transistor, and

the output interconnect is connected to a drain of the amplifier transistor.

10. (New) The solid-state imaging apparatus of claim 8,  
wherein the amplifier transistor is formed in the first pixel,  
the reset transistor is formed in the second pixel, and  
a distance and direction from the first photodiode to the amplifier transistor are  
substantially equal to a distance and direction from the second photodiode to the reset transistor.

11. (New) The solid-state imaging apparatus of claim 8, wherein a shape and size of the  
first pixel are substantially equal to a shape and size as that of the second pixel.

12. (New) The solid-state imaging apparatus of claim 8, wherein the solid-state imaging  
apparatus comprises a plurality of units, and  
each of the units includes only the first pixel, the second pixel, the reset transistor and the  
amplifier transistor.

13. (New) The solid-state imaging apparatus of claim 8, wherein the amplifier transistor  
and the reset transistor are formed in the second pixel and a drain of the reset transistor is a  
source of the amplifier transistor.

14. (New) The solid-state imaging apparatus of claim 8, further comprising:  
a row-select unit formed on the substrate, and  
a column-select unit formed on the substrate,  
wherein gates of the first transfer transistor and the second transfer transistor are  
connected to the row select unit, and  
a drain of the amplifier transistor is connected to the column-select unit.